Product data sheet

1. General description

Ultrafast diode in a TO3PF package.

2. Features and benefits

- Isolated plastic package
- Low leakage current
- · Low reverse recovery current
- · Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- · Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- · Half-bridge / full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Table 1. Quick	reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h \leq 73 °C; square-wave; Fig. 1; Fig. 2; Fig. 3	-	-	30	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; square-wave	-	-	60	Α
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 4</u>	-	-	170	Α
		t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN	-	-	190	Α
Static charac	teristics					
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.35	1.8	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.96	-	V
Dynamic cha	racteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	37	65	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 ^{\circ}C; Fig. 7$	-	85	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_i = 125 \text{ °C}; Fig. 7$	-	138	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode	mb O _ O	K — A
2	K	cathode		001aaa020
3	Α	anode	0 0	
mb	n.c.	mounting base; isolated	TO3PF	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYV30JT-600P	TO3PF	Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack'	TO3PF		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h \leq 73 °C; square-wave; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	30	Α
I _{O(AV)}	average output current	$\delta = 0.5$; $T_h \le 73$ °C; SQW	-	60	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; square-wave	-	60	А
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 4</u>	-	170	Α
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN	-	190	Α
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

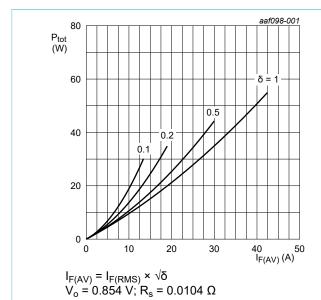


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; typical values

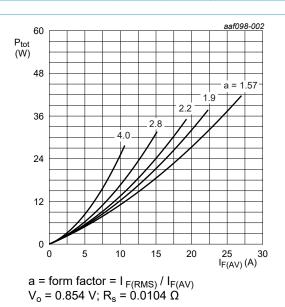
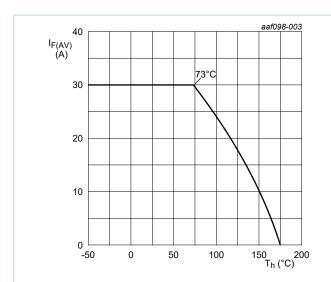


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; typical values





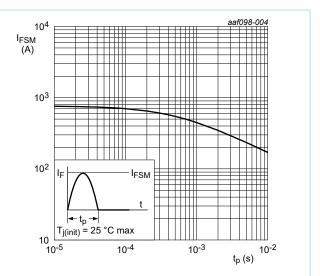


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	With heatsink compound; Fig. 5	-	2.3	2.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W

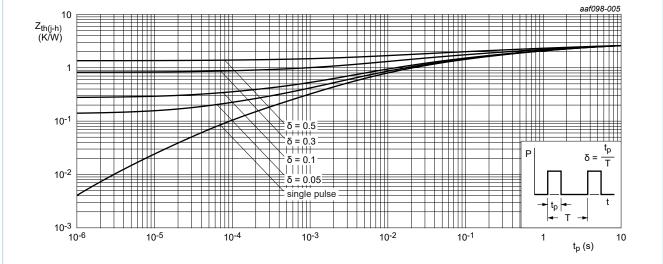
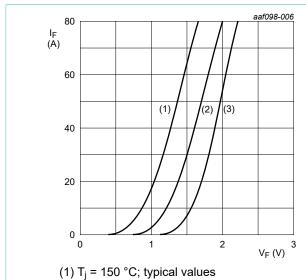


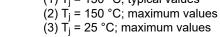
Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.35	1.8	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.96	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	500	μA
Dynamic ch	naracteristics		·			
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	37	65	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	85	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	138	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 \text{ °C}$	-	11	-	Α
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}$	-	18	-	Α
Q _r	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	461	-	nC
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _i = 125 °C; <u>Fig. 7</u>	-	1227	-	nC







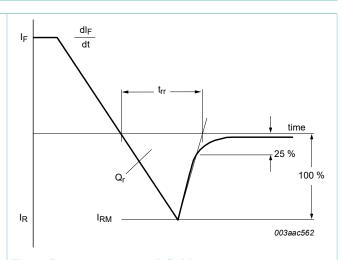
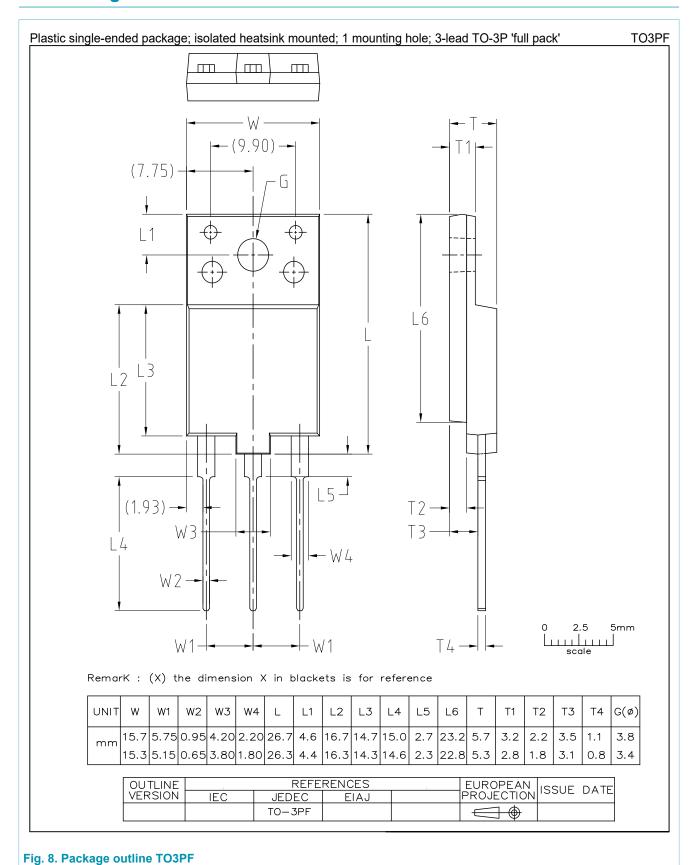


Fig. 7. Reverse recovery definitions; ramp recovery

10. Package outline

BYV30JT-600P



11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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BYV30JT-600P

Ultrafast recovery diode

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For more information, please visit: http://www.ween-semi.com
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